

SNXH80T120L2Q0SG

T-Type, Neutral Point Clamp Module

This high-density, integrated power module combines high-performance IGBTs with rugged anti-parallel diodes for sine wave inverter applications.

Features

- Extremely Efficient Trench IGBT with Fieldstop Technology
- Module Design Offers High Power Density
- Low Inductive Layout

Typical Applications

- Solar Inverters
- Uninterruptable Power Supplies

ABSOLUTE MAXIMUM RATINGS

Rating	Symbol	Value	Unit
--------	--------	-------	------

BRIDGE IGBT

Collector-emitter voltage	V_{CES}	1200	V
Collector current $T_h = 80^\circ\text{C}$	I_C	65	A
Pulsed Collector Current, T_{pulse} Limited by T_{jmax}	I_{CM}	260	A
Gate-emitter voltage	V_{GE}	± 20	V
Power Dissipation per IGBT $T_j = T_{jmax}$ $T_h = 80^\circ\text{C}$	P_{total}	146	W
Short Circuit Withstand Time $V_{GE} = 15\text{ V}$, $V_{CE} = 600\text{ V}$, $T_J \leq 150^\circ\text{C}$	T_{SC}	10	μs

NEUTRAL POINT IGBT

Collector-emitter voltage (Bridge)	V_{CES}	600	V
Collector current $@ T_h = 80^\circ\text{C}$	I_C	59	A
Pulsed Collector Current, T_{pulse} Limited by T_{jmax}	I_{CM}	235	A
Gate-emitter voltage	V_{GE}	± 20	V
Power Dissipation per IGBT $T_j = T_{jmax}$ $T_h = 80^\circ\text{C}$	P_{total}	66	W
Short Circuit Withstand Time $V_{GE} = 15\text{ V}$, $V_{CE} = 400\text{ V}$, $T_J \leq 150^\circ\text{C}$	T_{SC}	5	μs

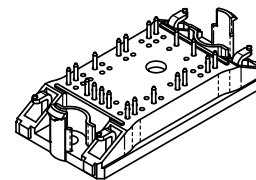
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



ON Semiconductor®

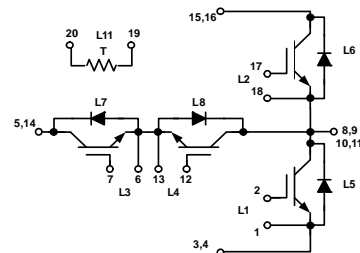
www.onsemi.com

80 A, 1200 V (Bridge)
50 A, 600 V (Neutral Point Clamp)
T – Type Neutral Point Clamp

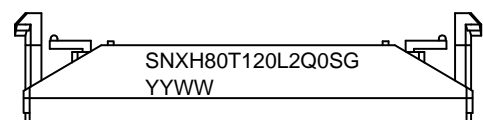


Q0PACK
CASE 180AB

SCHEMATIC



MARKING DIAGRAM



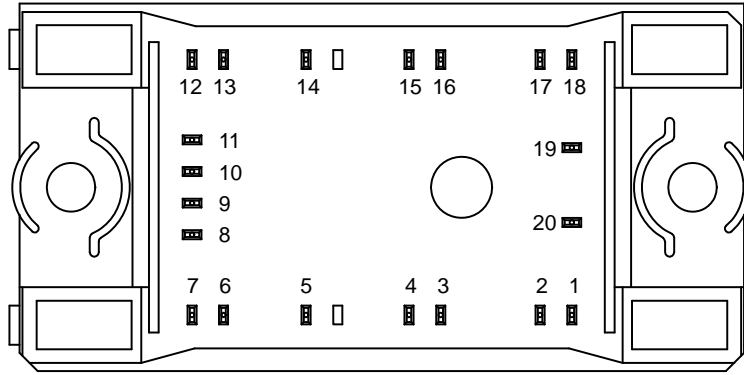
YYWW = Year and Work Week Code

ORDERING INFORMATION

See detailed ordering and shipping information in the dimensions section on page 13 of this data sheet.

SNXH80T120L2Q0SG

PIN ASSIGNMENTS



ABSOLUTE MAXIMUM RATINGS

Rating	Symbol	Value	Unit
BRIDGE DIODE			
Peak Repetitive Voltage	V_{RRM}	1200	V
Forward Current, DC @ $T_C = 80^\circ\text{C}$	I_F	41	A
Power Dissipation per Diode $T_j = T_{jmax}$ $T_h = 80^\circ\text{C}$	P_{total}	69	W
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)	I_{FSM}	300	A
I^2t – value (Surge applied at rated load conditions halfwave, single phase, 60 Hz)	I^2t	373.5	A^2s

NEUTRAL POINT DIODE

Diode peak repetitive voltage	V_{RRM}	600	V
Forward Current, DC @ $T_h = 80^\circ\text{C}$	I_F	36	A
Power Dissipation per Diode $T_j = T_{jmax}$ $T_h = 80^\circ\text{C}$	P_{total}	51	W
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)	I_{FSM}	500	A
I^2t – value (Surge applied at rated load conditions halfwave, single phase, 60 Hz)	I^2t	1037.5	A^2s

THERMAL & SAFETY CHARACTERISTICS

Rating	Symbol	Value	Unit
Maximum junction temperature range IGBT Diode	T_J	175 175	$^\circ\text{C}$
Storage temperature range	T_{stg}	-40 to 150	$^\circ\text{C}$
Operating Temperature under Switching conditions	T_{VJOP}	-40 to 150	$^\circ\text{C}$
Isolation test voltage, $t = 1$ min, 60 Hz	V_{is}	2500	Vac
Creepage distance		12.7	mm
Clearance		12.7	mm

SNXH80T120L2Q0SG

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

Parameter	Test Conditions	Symbol	Min	Typ	Max	Unit	
HALF BRIDGE IGBT CHARACTERISTICS							
Collector-emitter saturation voltage	V _{GE} = 15 V, I _C = 80 A, T _J = 25°C V _{GE} = 15 V, I _C = 80 A, T _J = 150°C	V _{CE(sat)}	1.7	2.17 2.20	2.7	V	
Gate-emitter threshold voltage	V _{GE} = V _{CE} , I _C = 1.5 mA	V _{GE(TH)}	5.0	6.0	6.5	V	
Collector-emitter cutoff current	V _{GE} = 0 V, V _{CE} = 1200 V	I _{CES}	–	–	200	μA	
Gate leakage current	V _{GE} = 20 V, V _{CE} = 0 V	I _{GES}	–	–	1.2	μA	
Turn-on delay time	T _J = 25°C V _{CE} = 350 V, I _C = 56 A V _{GE} = ±15 V, R _G = 4 Ω	t _{d(on)}	–	35	–	ns	
Rise time		t _r	–	28	–		
Turn-off delay time		t _{d(off)}	–	280	–		
Fall time		t _f	–	28	–		
Turn on switching loss		E _{on}	–	0.670	–		mJ
Turn off switching loss		E _{off}	–	1.3	–		
Turn-on delay time	T _J = 150°C V _{CE} = 350 V, I _C = 56 A V _{GE} = ±15 V, R _G = 4 Ω	t _{d(on)}	–	80	–	ns	
Rise time		t _r	–	30	–		
Turn-off delay time		t _{d(off)}	–	320	–		
Fall time		t _f	–	230	–		
Turn on switching loss		E _{on}	–	0.975	–		mJ
Turn off switching loss		E _{off}	–	3.00	–		
Input capacitance	V _{CE} = 20 V, V _{GE} = 0 V, f = 10 KHz	C _{ies}	–	19940	–	pF	
Output capacitance		C _{oes}	–	592	–		
Reverse transfer capacitance		C _{res}	–	383	–		
Gate charge total	V _{CE} = 960 V, I _C = 40 A, V _{GE} = ±15 V	Q _g	–	840	–	nC	
Thermal Resistance, chip-to-heatsink	Thermal grease thickness ≤ 50 μm λ = 1 W/mK	R _{θJH}		0.65		°C/W	

HALF BRIDGE DIODE CHARACTERISTICS

Forward voltage	V _{GE} = 0 V, I _F = 50 A, T _J = 25°C V _{GE} = 0 V, I _F = 50 A, T _J = 150°C	V _F	–	1.81 1.90	2.4	V
Reverse recovery time	T _J = 25°C V _{CE} = 350 V, I _C = 56 A V _{GE} = ±15 V, R _G = 4 Ω	t _{rr}	–	0.12	–	μs
Reverse recovery charge		Q _{rr}	–	4.7	–	μC
Peak reverse recovery current		I _{rrm}	–	135	–	A
Peak rate of fall of recovery current		di/dt _{max}	–	7200	–	A/μs
Reverse recovery energy		E _{rr}	–	1.37	–	mJ
Reverse recovery time	T _J = 150°C V _{CE} = 350 V, I _C = 56 A V _{GE} = ±15 V, R _G = 4 Ω	t _{rr}	–	0.14	–	μs
Reverse recovery charge		Q _{rr}	–	7.65	–	μC
Peak reverse recovery current		I _{rrm}	–	138	–	A
Peak rate of fall of recovery current		di/dt _{max}	–	4900	–	A/μs
Reverse recovery energy		E _{rr}	–	2.15	–	mJ
Thermal Resistance, chip-to-heatsink	Thermal grease thickness ≤ 50 μm λ = 1 W/mK	R _{θJH}		1.38		°C/W

NEUTRAL POINT CLAMP IGBT CHARACTERISTICS

Collector-emitter saturation voltage	V _{GE} = 15 V, I _C = 30 A, T _J = 25°C V _{GE} = 15 V, I _C = 30 A, T _J = 150°C	V _{CE(sat)}	1.1	1.3 1.3	1.6	V
Gate-emitter threshold voltage	V _{GE} = V _{CE} , I _C = 1.2 mA	V _{GE(TH)}	5.0	5.7	6.5	V
Collector-emitter cutoff current	V _{GE} = 0 V, V _{CE} = 600 V	I _{CES}	–	–	100	μA
Gate leakage current	V _{GE} = 20 V, V _{CE} = 0 V	I _{GES}	–	–	0.60	μA

SNXH80T120L2Q0SG

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

Parameter	Test Conditions	Symbol	Min	Typ	Max	Unit
NEUTRAL POINT CLAMP IGBT CHARACTERISTICS						
Turn-on delay time	T _J = 25°C V _{CE} = 350 V, I _C = 56 A V _{GE} = ±15 V, R _G = 4 Ω	t _{d(on)}	–	46	–	ns
Rise time		t _r	–	16	–	
Turn-off delay time		t _{d(off)}	–	125	–	
Fall time		t _f	–	60	–	
Turn on switching loss		E _{on}	–	0.668	–	mJ
Turn off switching loss		E _{off}	–	0.76	–	
Turn-on delay time	T _J = 150°C V _{CE} = 350 V, I _C = 56 A V _{GE} = ±15 V, R _G = 4 Ω	t _{d(on)}	–	48	–	ns
Rise time		t _r	–	22	–	
Turn-off delay time		t _{d(off)}	–	200	–	
Fall time		t _f	–	134	–	
Turn on switching loss		E _{on}	–	1.1	–	mJ
Turn off switching loss		E _{off}	–	2.5	–	
Input capacitance	V _{CE} = 20 V, V _{GE} = 0 V, f = 10 KHz	C _{ies}	–	9900	–	pF
Output capacitance		C _{oes}	–	270	–	
Reverse transfer capacitance		C _{res}	–	270	–	
Gate charge total	V _{CE} = 480 V, I _C = 75 A, V _{GE} = ±15 V	Q _G	–	390	–	nC
Thermal Resistance, chip-to-heatsink	Thermal grease thickness ≤ 50 μm λ = 1 W/mK	R _{θJH}		1.35		°C/W

NEUTRAL POINT CLAMP DIODE CHARACTERISTICS

Forward voltage	V _{GE} = 0 V, I _F = 60 A, T _J = 25°C V _{GE} = 0 V, I _F = 60 A, T _J = 150°C	V _F	–	1.7 1.8	2.0 –	V
Reverse recovery time	T _J = 25°C V _{CE} = 350 V, I _C = 56 A V _{GE} = ±15 V, R _G = 4 Ω	t _{rr}	–	0.04	–	μs
Reverse recovery charge		Q _{rr}	–	1.1	–	μC
Peak reverse recovery current		I _{rrm}	–	65	–	A
Peak rate of fall of recovery current		di/dt _{max}	–	6600	–	A/μs
Reverse recovery energy		E _{rr}	–	0.384	–	mJ
Reverse recovery time	T _J = 150°C V _{CE} = 350 V, I _C = 56 A V _{GE} = ±15 V, R _G = 4 Ω	t _{rr}	–	0.1	–	μs
Reverse recovery charge		Q _{rr}	–	3.3	–	μC
Peak reverse recovery current		I _{rrm}	–	68	–	A
Peak rate of fall of recovery current		di/dt _{max}	–	1733	–	A/μs
Reverse recovery energy		E _{rr}	–	0.74	–	mJ
Thermal Resistance, chip-to-heatsink	Thermal grease thickness ≤ 50 μm λ = 1 W/mK	R _{θJH}		1.86		°C/W

THERMISTOR CHARACTERISTICS

Normal resistance		R		22		kΩ
Nominal resistance	T = 100°C	R		1468		Ω
Deviation of R25		ΔR/R	–5		5	%
Power dissipation		P _D		200		mW
Power dissipation constant				2		mW/K
B-value	B(25/50), tol ±3%				3950	K
B-value	B(25/100), tol ±3%				3998	K
NTC reference					B	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

SNXH80T120L2Q0SG

TYPICAL CHARACTERISTICS – HALF BRIDGE

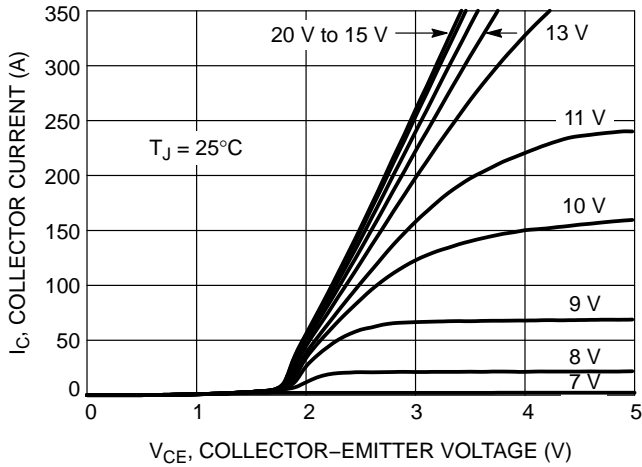


Figure 1. Output Characteristics

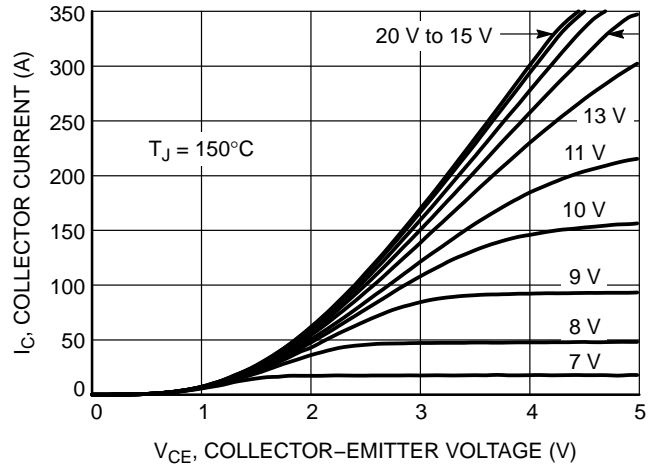


Figure 2. Output Characteristics

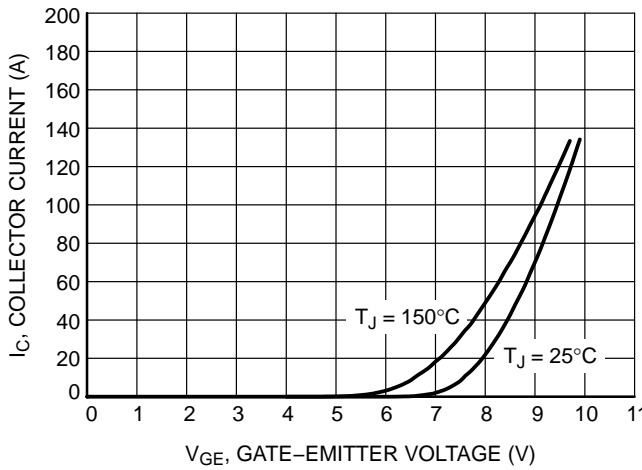


Figure 3. Typical Transfer Characteristics

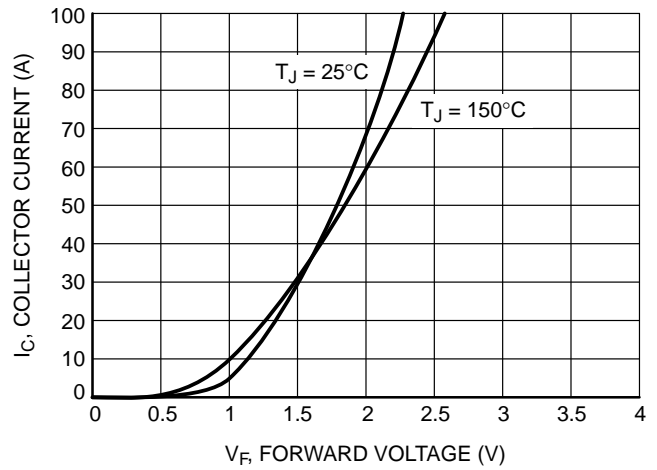


Figure 4. Diode Forward Characteristics

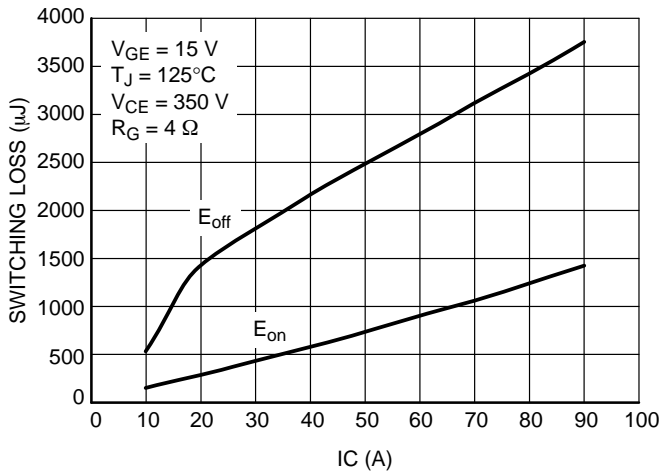


Figure 5. Typical Switching Loss vs. IC

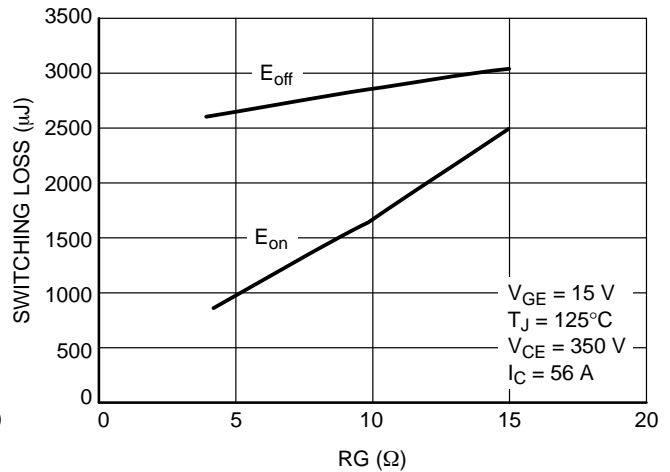


Figure 6. Typical Switching Loss vs. RG

SNXH80T120L2Q0SG

TYPICAL CHARACTERISTICS – HALF BRIDGE

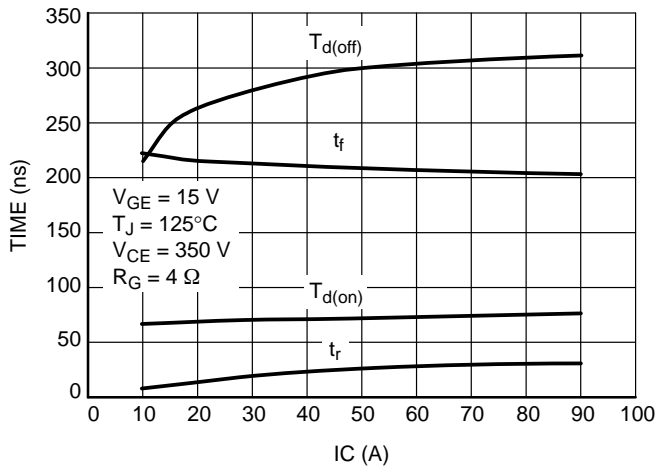


Figure 7. Typical Switching Time vs. IC

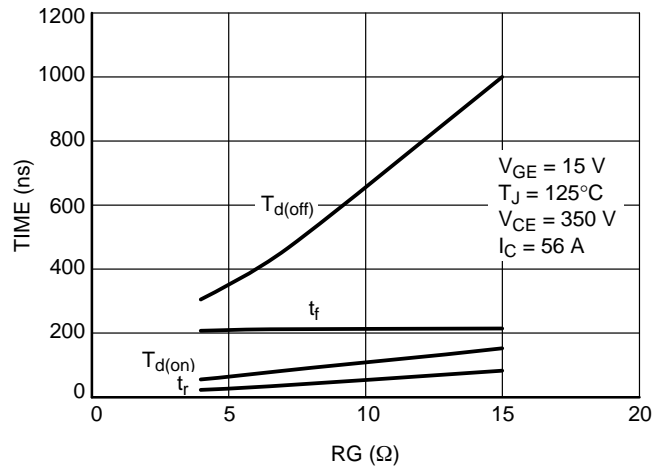


Figure 8. Typical Switching Time vs. RG

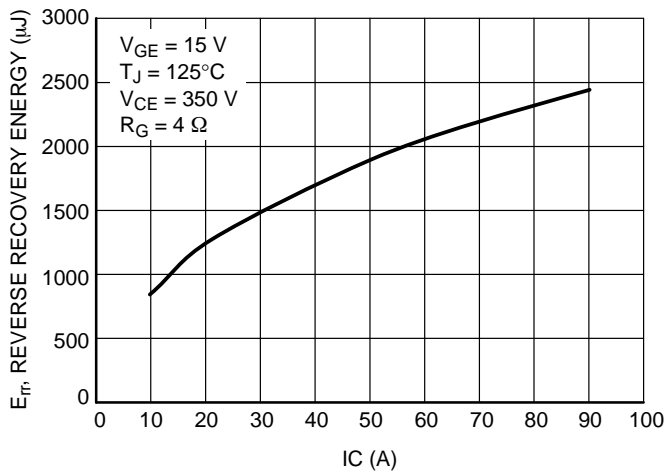


Figure 9. Typical Reverse Recovery Energy Loss vs. IC

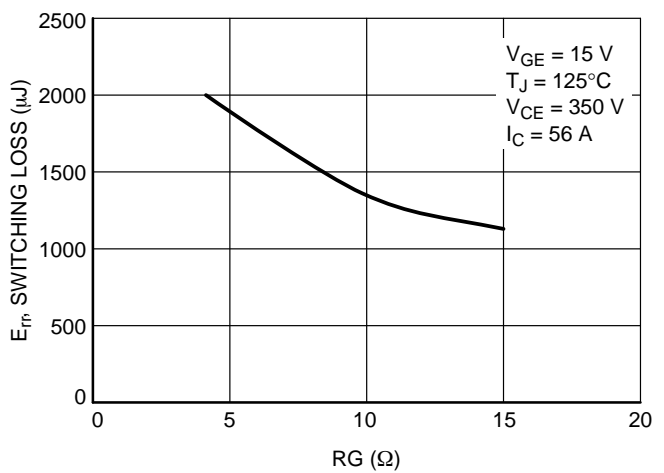


Figure 10. Typical Reverse Recovery Energy Loss vs. RG

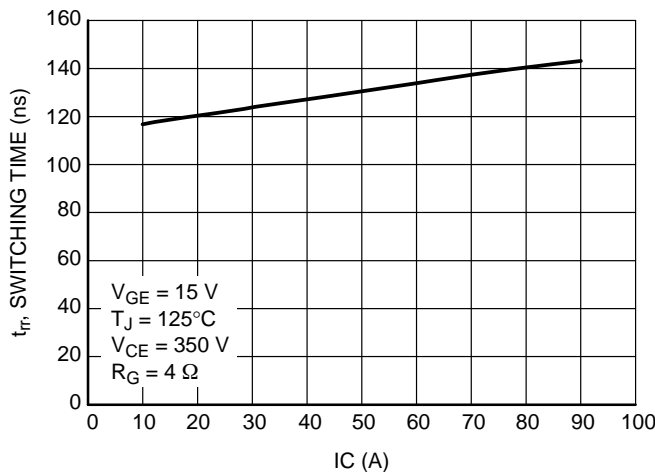


Figure 11. Typical Reverse Recovery Time vs. IC

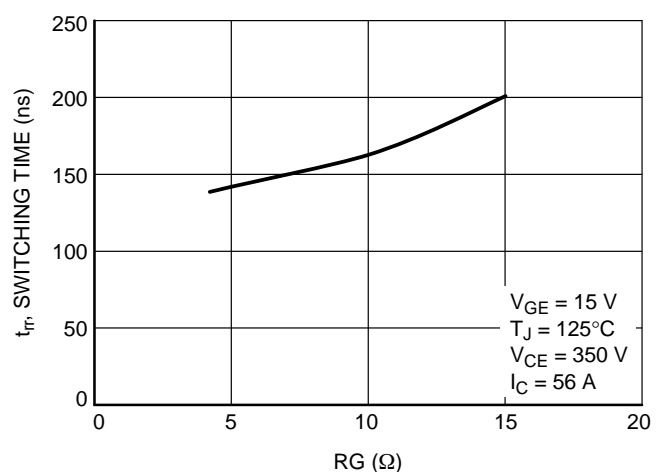


Figure 12. Typical Reverse Recovery Time vs. RG

SNXH80T120L2Q0SG

TYPICAL CHARACTERISTICS – HALF BRIDGE

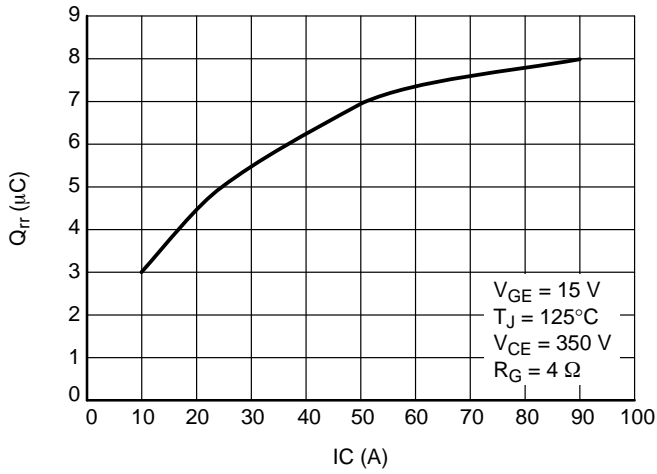


Figure 13. Typical Reverse Recovery Charge vs. IC

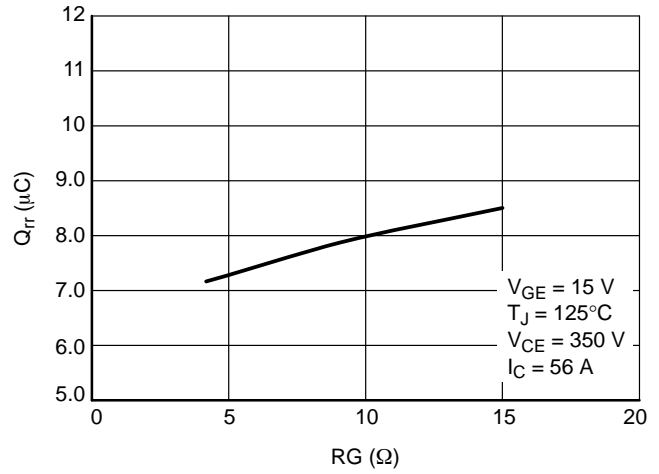


Figure 14. Typical Reverse Recovery Charge vs. RG

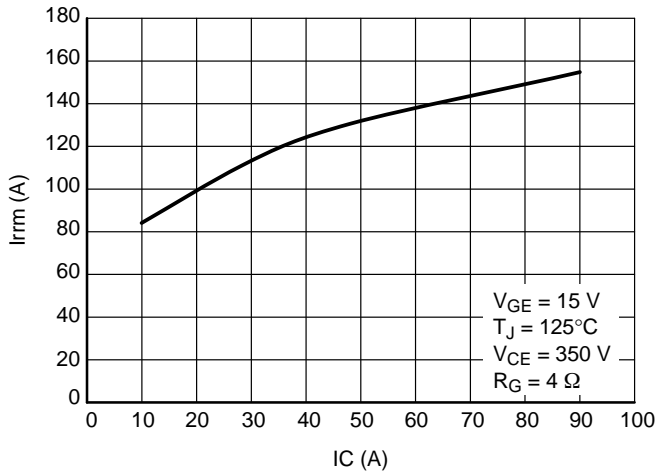


Figure 15. Typical Reverse Recovery Current vs. IC

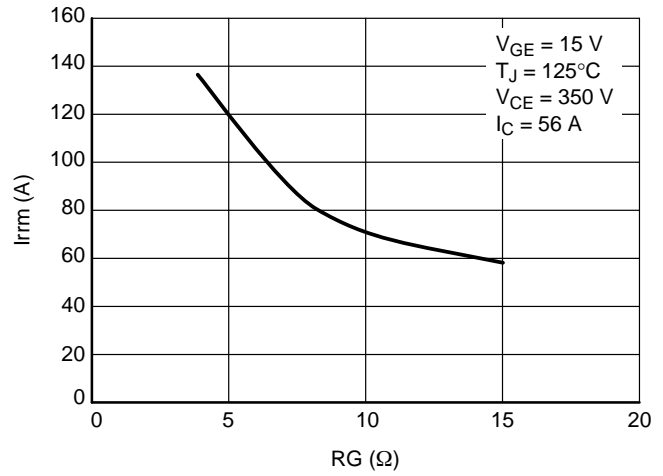


Figure 16. Typical Reverse Recovery Current vs. RG

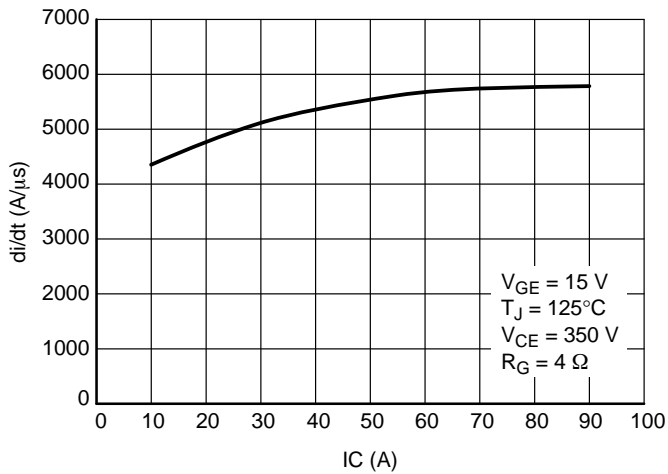


Figure 17. Typical di/dt vs. IC

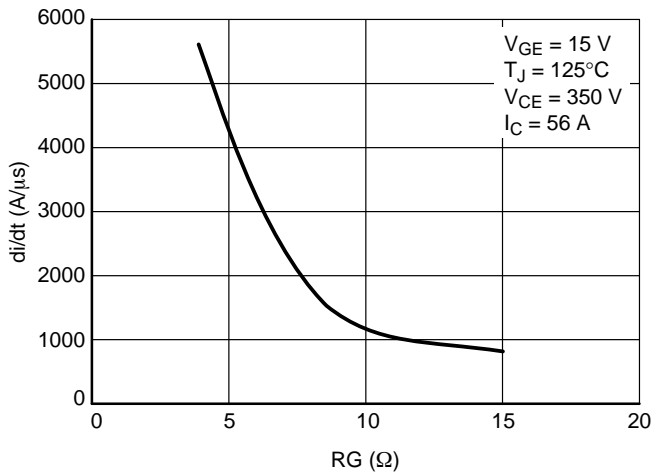


Figure 18. Typical di/dt vs. RG

SNXH80T120L2Q0SG

TYPICAL CHARACTERISTICS – HALF BRIDGE

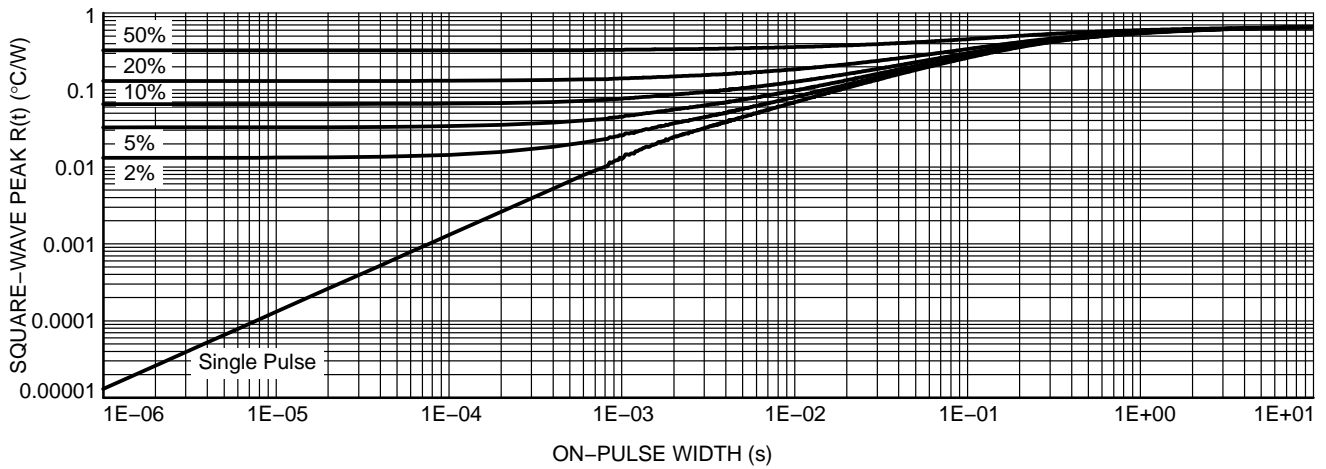


Figure 19. IGBT Transient Thermal Impedance

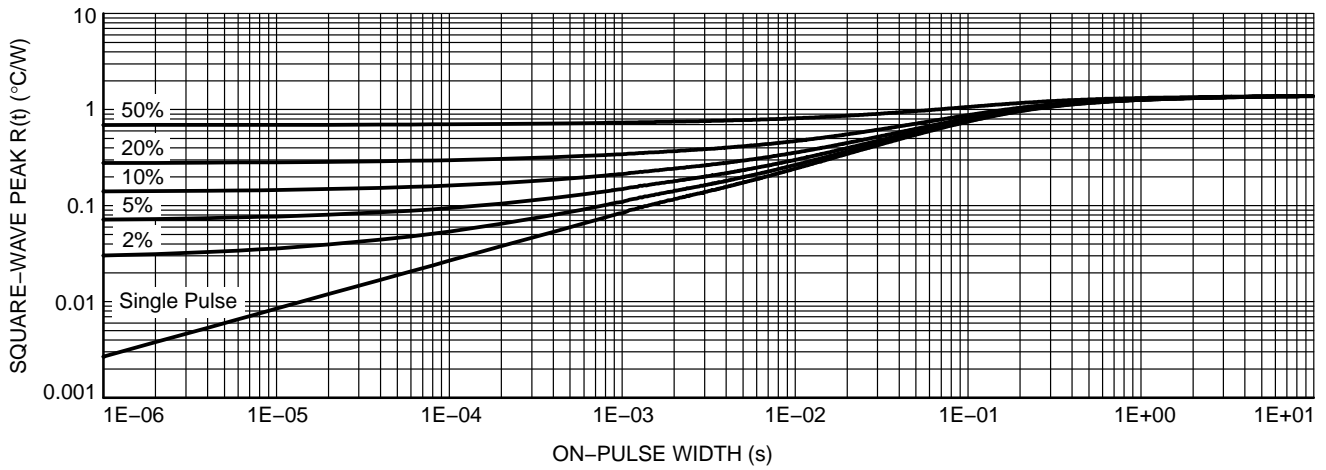


Figure 20. Diode Transient Thermal Impedance

SNXH80T120L2Q0SG

TYPICAL CHARACTERISTICS – NEUTRAL POINT

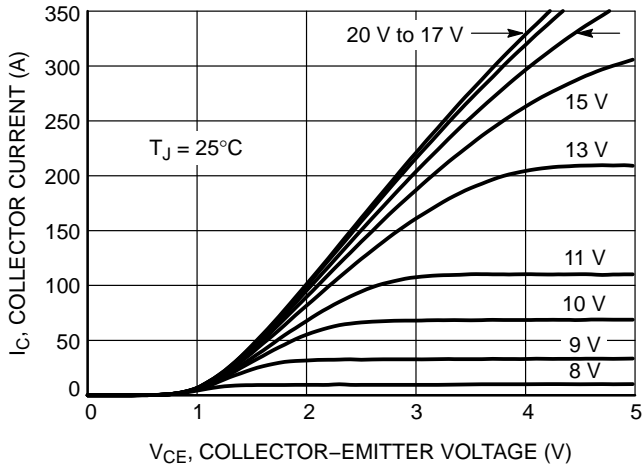


Figure 21. Output Characteristics

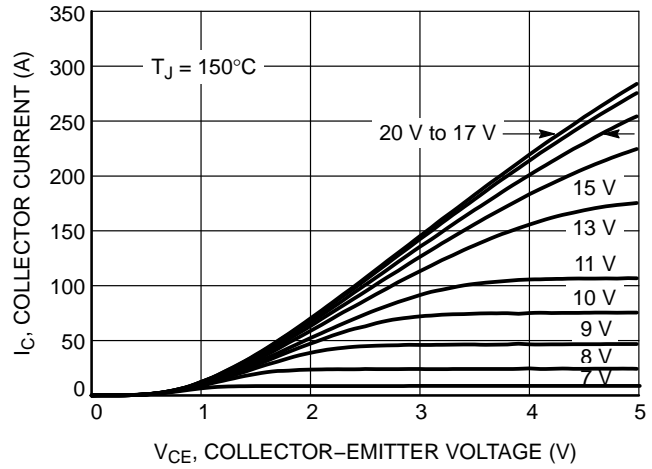


Figure 22. Output Characteristics

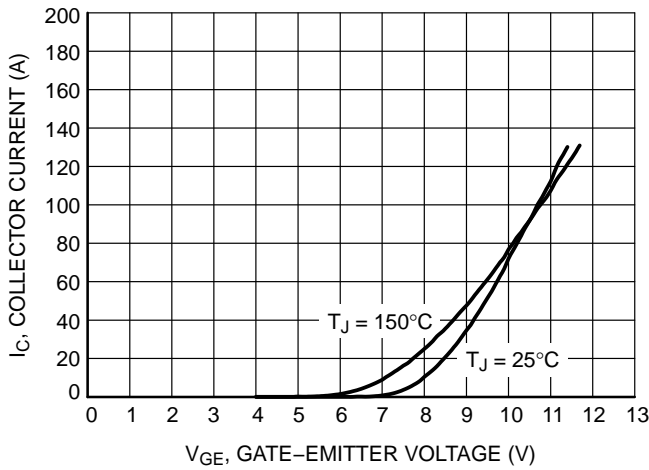


Figure 23. Typical Transfer Characteristics

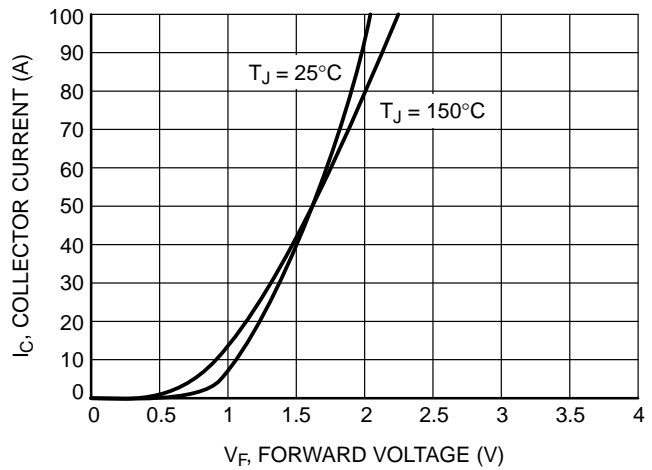


Figure 24. Diode Forward Characteristics

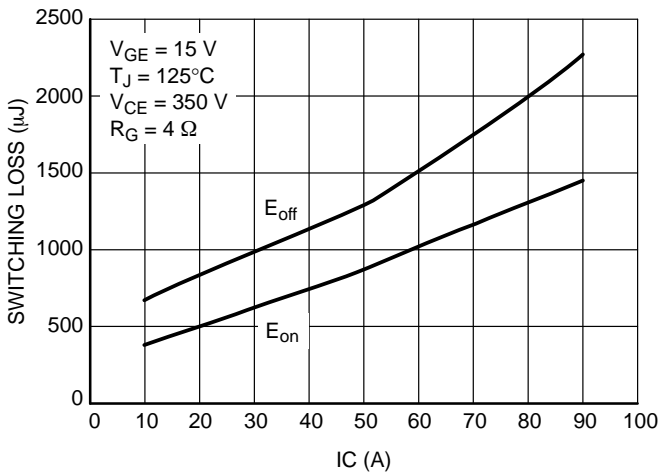


Figure 25. Typical Switching Loss vs. I_C

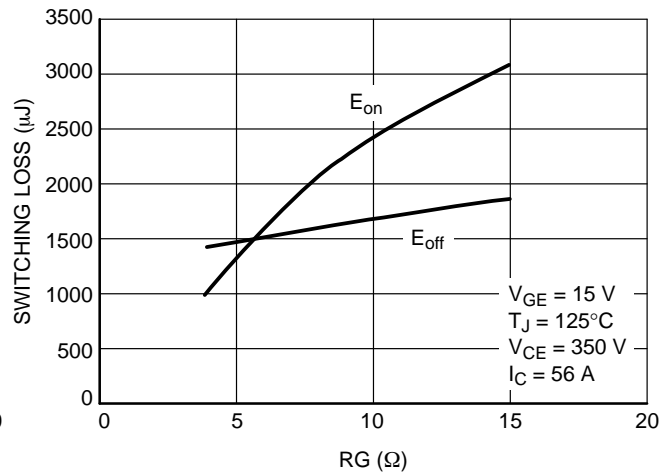


Figure 26. Typical Switching Loss vs. R_G

SNXH80T120L2Q0SG

TYPICAL CHARACTERISTICS – NEUTRAL POINT

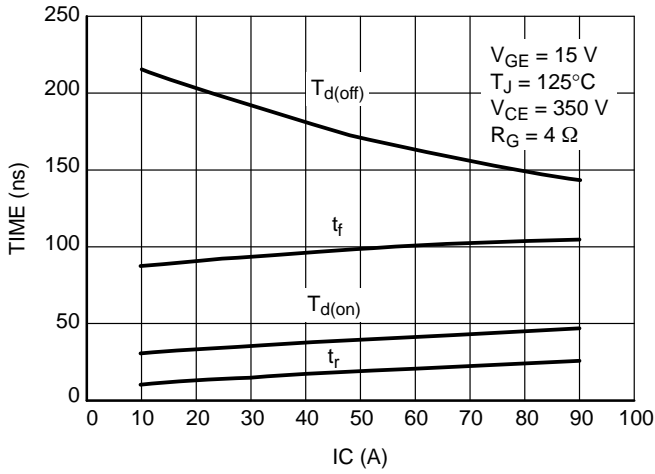


Figure 27. Typical Switching Time vs. IC

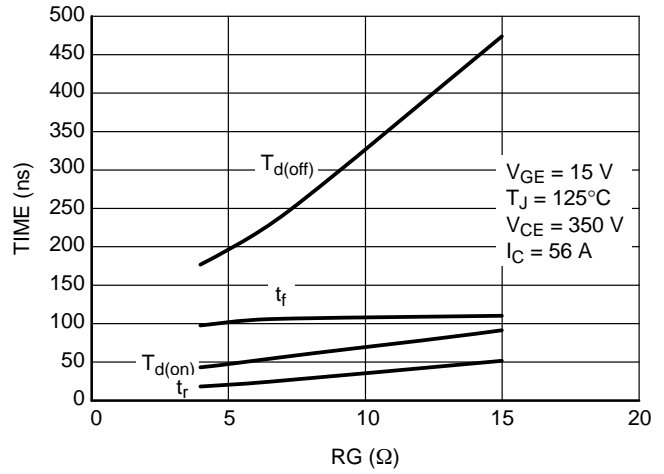


Figure 28. Typical Switching Time vs. RG

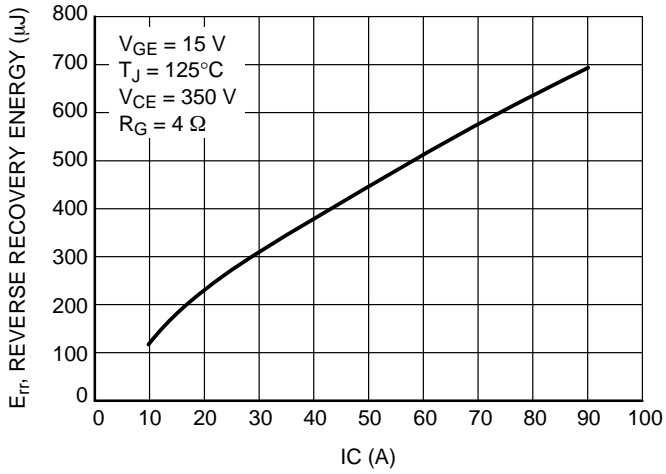


Figure 29. Typical Reverse Recovery Energy Loss vs. IC

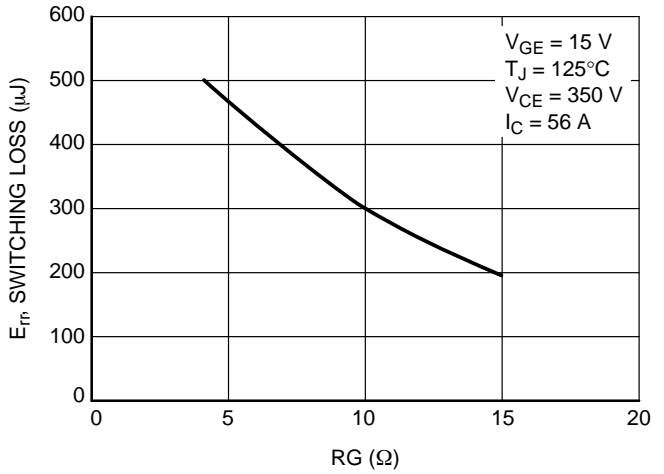


Figure 30. Typical Reverse Recovery Energy Loss vs. RG

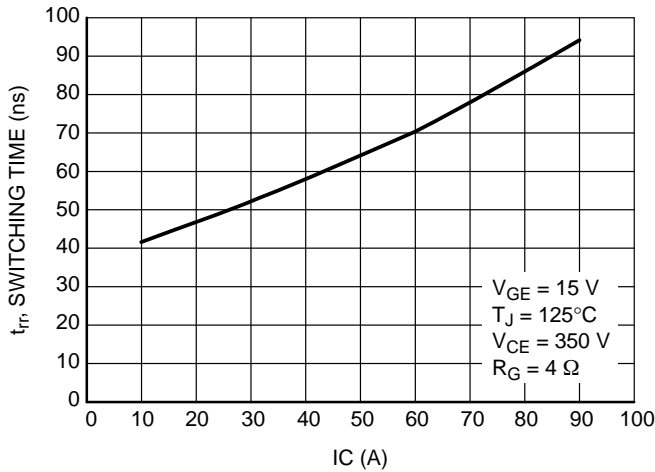


Figure 31. Typical Reverse Recovery Time vs. IC

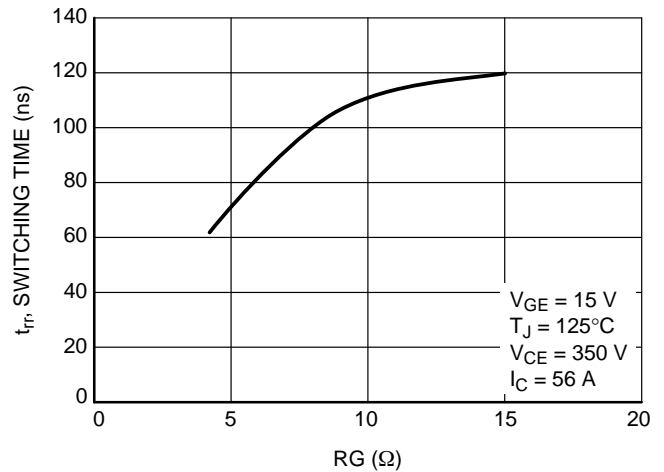


Figure 32. Typical Reverse Recovery Time vs. RG

SNXH80T120L2Q0SG

TYPICAL CHARACTERISTICS – NEUTRAL POINT

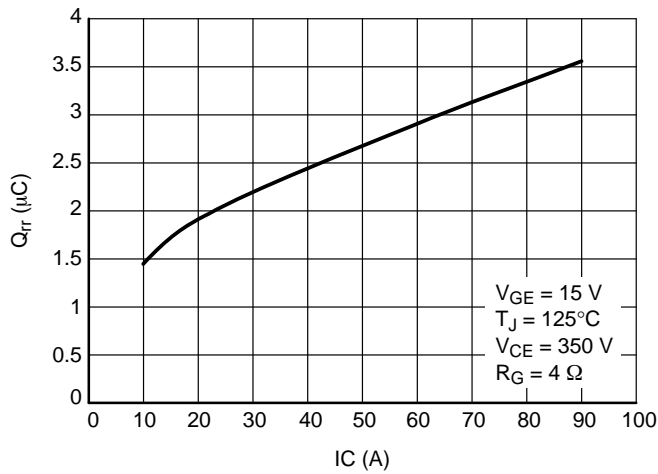


Figure 33. Typical Reverse Recovery Charge vs. IC

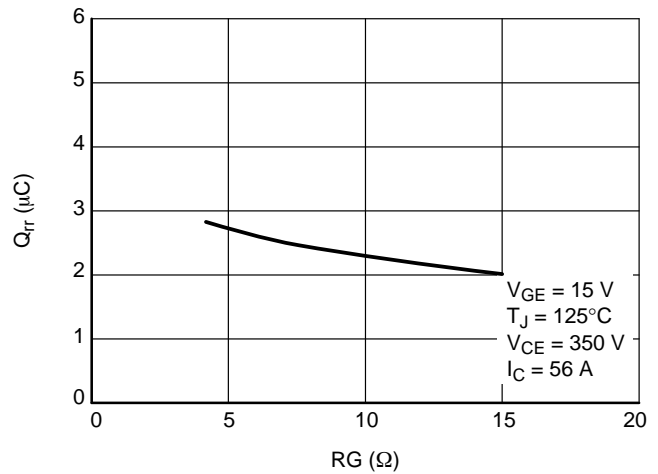


Figure 34. Typical Reverse Recovery Charge vs. RG

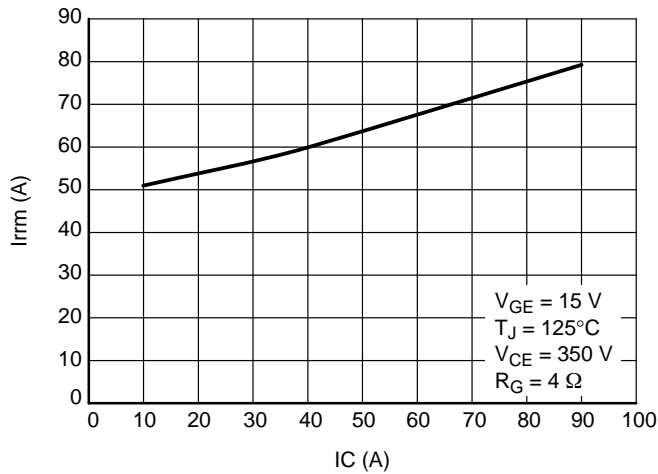


Figure 35. Typical Reverse Recovery Current vs. IC

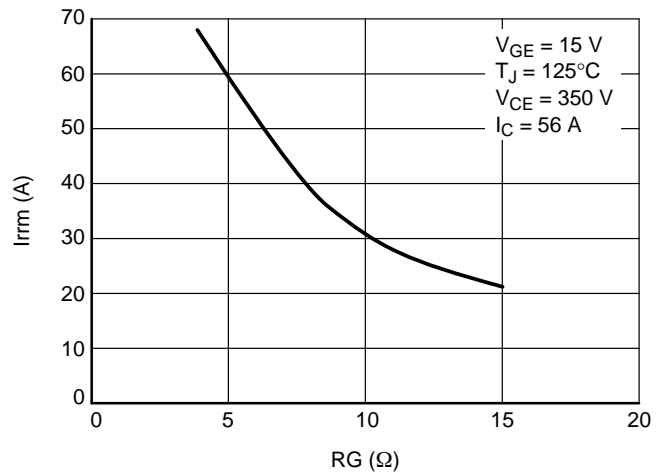


Figure 36. Typical Reverse Recovery Current vs. RG

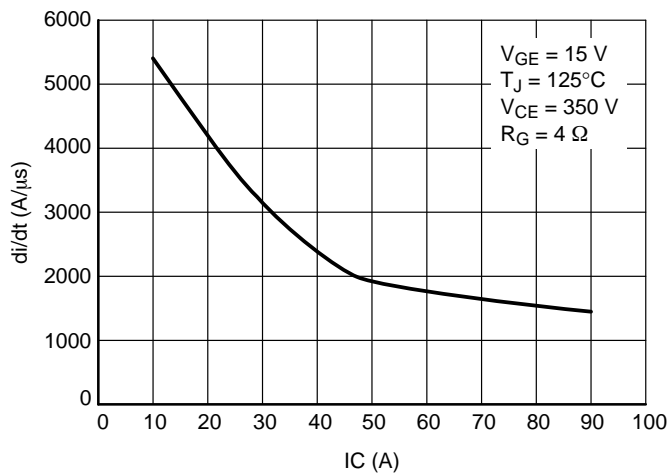


Figure 37. Typical di/dt vs. IC

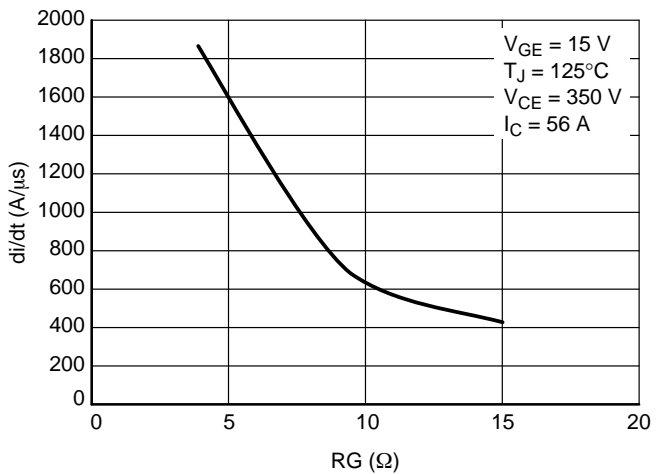


Figure 38. Typical di/dt vs. RG

SNXH80T120L2Q0SG

TYPICAL CHARACTERISTICS – NEUTRAL POINT

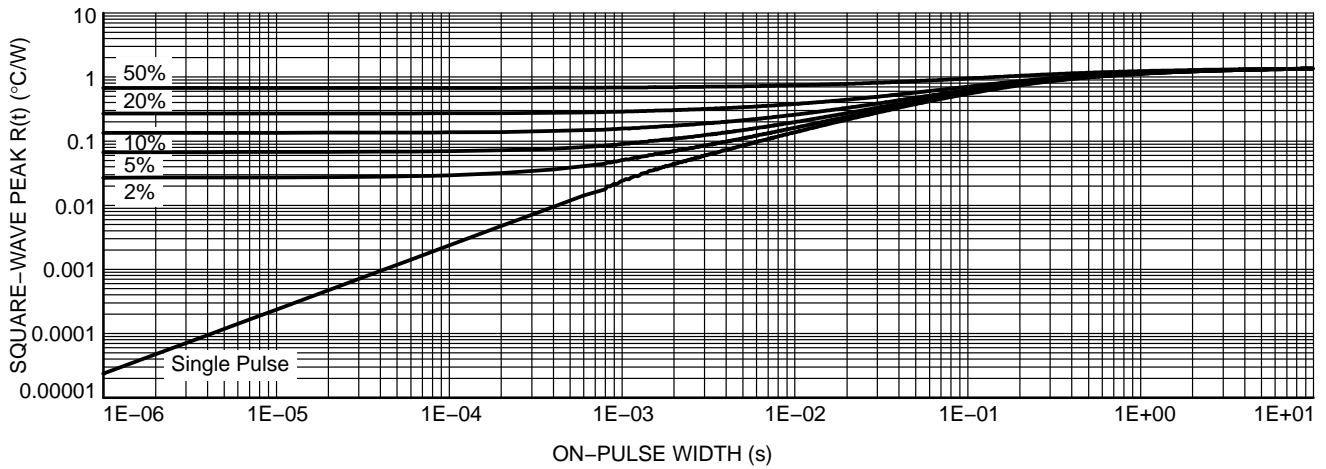


Figure 39. IGBT Transient Thermal Impedance

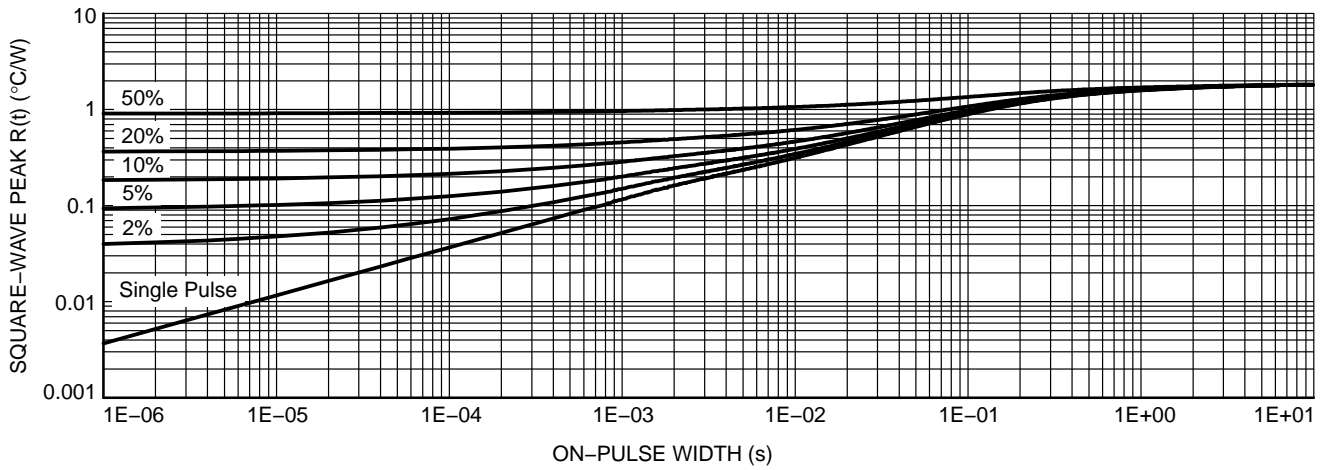


Figure 40. Diode Transient Thermal Impedance

SNXH80T120L2Q0SG

THERMISTOR CHARACTERISTICS

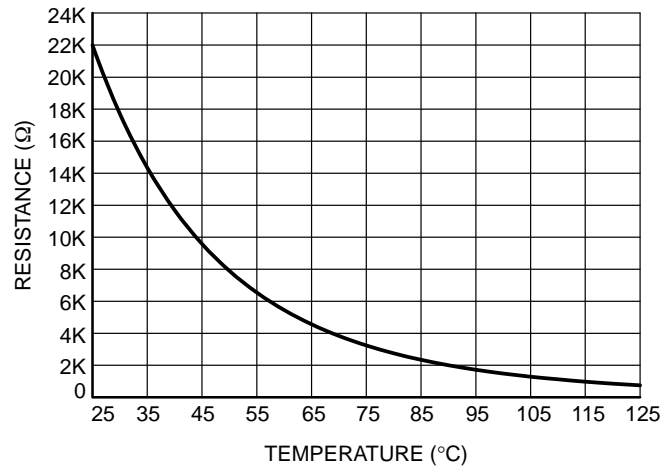


Figure 41. Thermistor Characteristics

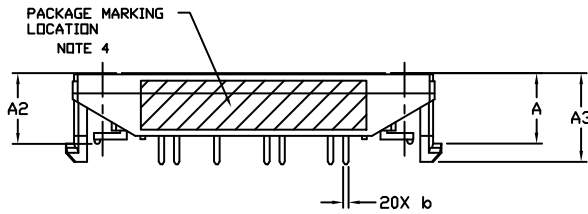
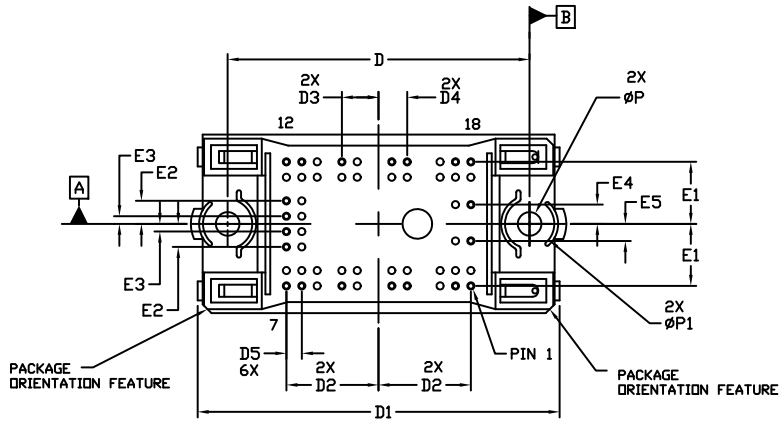
ORDERING INFORMATION

Orderable Part Number	Package	Shipping
SNXH80T120L2Q0SG (Solder Pin)	Q0PACK – Case 180AB (Pb-Free and Halide-Free)	24 Units / Blister Tray

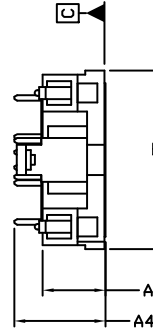
SNXH80T120L2Q0SG

PACKAGE DIMENSIONS

PIM20, 55x32.5 / Q0PACK
CASE 180AB
ISSUE A



⌀0.40 ⓈC|A|B



NOTES:

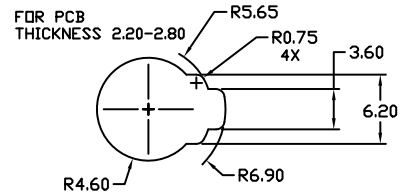
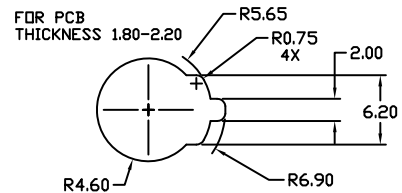
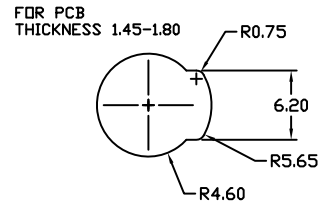
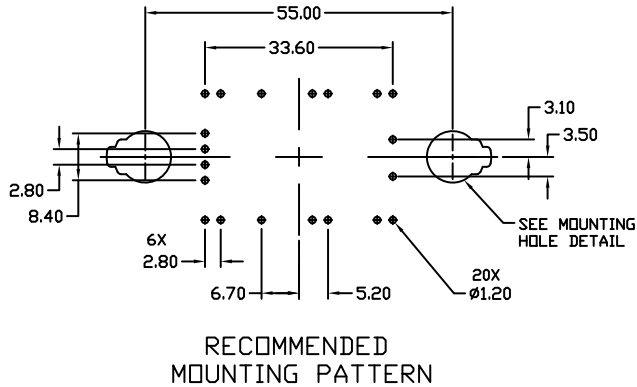
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
2. CONTROLLING DIMENSION: MILLIMETERS
3. DIMENSION b APPLIES TO THE PLATED TERMINALS AND ARE MEASURED BETWEEN 1.00 AND 3.00 FROM TERMINAL TIP.
4. PACKAGE MARKING IS LOCATED AS SHOWN ON THE SIDE OPPOSITE THE PACKAGE ORIENTATION FEATURES.

DIM	MILLIMETERS	
	MIN.	NDM.
A	13.10	14.10
A1	10.75	11.75
A2	12.20	13.20
A3	15.45	16.45
A4	16.40	REF
b	0.95	1.05
D	54.80	55.20
D1	65.70	70.10
D2	16.80	BSC
D3	6.70	BSC
D4	5.20	BSC
D5	2.80	BSC
E	32.00	33.00
E1	11.30	BSC
E2	4.20	BSC
E3	1.40	BSC
E4	3.50	BSC
E5	3.10	BSC
P	4.10	4.50
P1	8.50	9.50


SNXH80T120L2Q0SG

PACKAGE DIMENSIONS

PIM20, 55x32.5 / Q0PACK
CASE 180AB
ISSUE A



MOUNTING HOLE DETAIL

ON Semiconductor and the  are registered trademarks of Semiconductor Components Industries, LLC (SCILLC) or its subsidiaries in the United States and/or other countries. SCILLC owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of SCILLC's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA
Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada
Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free
USA/Canada
Europe, Middle East and Africa Technical Support:
Phone: 421 33 790 2910
Japan Customer Focus Center
Phone: 81-3-5817-1050

ON Semiconductor Website: www.onsemi.com
Order Literature: <http://www.onsemi.com/orderlit>
For additional information, please contact your local Sales Representative

SNXH80T120L2Q0SG/D